## 2SD1138

## Silicon NPN Triple Diffused

## **HITACHI**

ADE-208-908 (Z) 1st. Edition Sep. 2000

#### **Application**

Low frequency high voltage power amplifier TV vertical deflection output complementary pair with 2SB861

#### **Outline**

TO-220AB

1. Base
2. Collector
(Flange)
3. Emitter



#### 2SD1138

### **Absolute Maximum Ratings** (Ta = 25°C)

Item	n Symbol		Unit	
Collector to base voltage	$V_{\text{CBO}}$	200	V	
Collector to emitter voltage	$V_{\text{CEO}}$	150	V	
Emitter to base voltage	$V_{EBO}$	6	V	
Collector current	I <sub>c</sub>	2	Α	
Collector peak current	I <sub>C (peak)</sub>	5	Α	
Collector power dissipation	P <sub>c</sub>	1.8	W	
	P <sub>c</sub> *1	30	W	
Junction temperature	Тј	150	°C	
Storage temperature	Tstg	-45 to +150	°C	

Note: 1. Value at  $T_c = 25^{\circ}C$ .

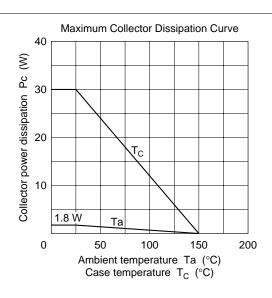
### **Electrical Characteristics** (Ta = 25°C)

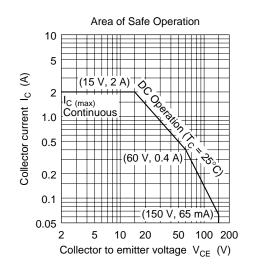
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	150	_	_	V	$I_{\rm C}$ = 50 mA, $R_{\rm BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_E = 5 \text{ mA}, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1	μΑ	V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0
DC current transfer ratio	h <sub>FE1</sub> *1	60		320		$V_{CE} = 4 \text{ V}, I_{C} = 50 \text{ mA}$
	h <sub>FE2</sub>	60	_	_		$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE (sat)}}$	_	_	3.0	V	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}^{*2}$
Base to emitter voltage	V <sub>BE</sub>	_	_	1.0	V	$V_{CB} = 4 \text{ V}, I_{C} = 50 \text{ mA}$
Collector output capacitance	Cob	_	20	_	pF	$V_{CB} = 100 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

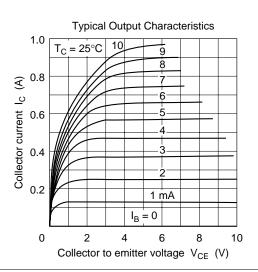
Note: 1. The 2SD1138 is grouped by  $h_{\text{FE1}}$  as follows.

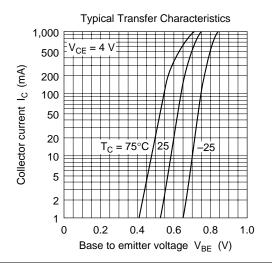
Pulse test.

В	С	D
60 to 120	100 to 200	160 to 320

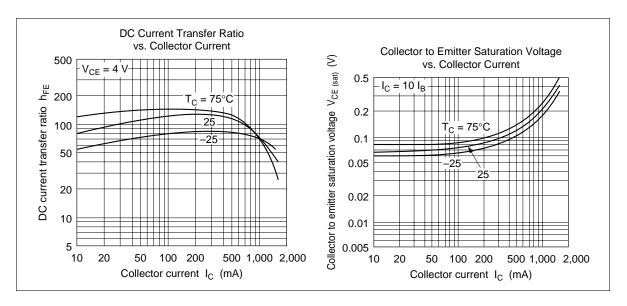




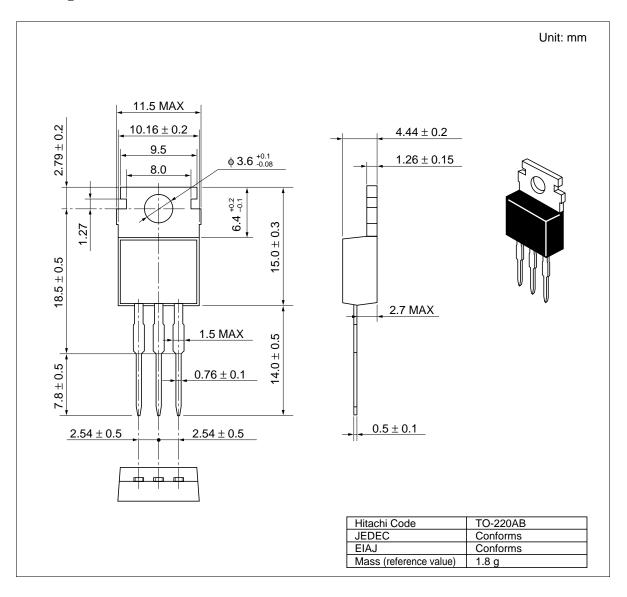




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### **Package Dimensions**



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